

**2002 23rd INTERNATIONAL CONFERENCE
ON MICROELECTRONICS**

PROCEEDINGS



Niš, Yugoslavia
12-15 May 2002

Volume 1

organized by
Yugoslavia IEEE Section - ED/SSC Chapter

under the co-sponsorship of
IEEE Electron Devices Society

with the cooperation of
IEEE Solid-State Circuits Society



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for

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J. Nicolics accepts the award from N. Stojadinović

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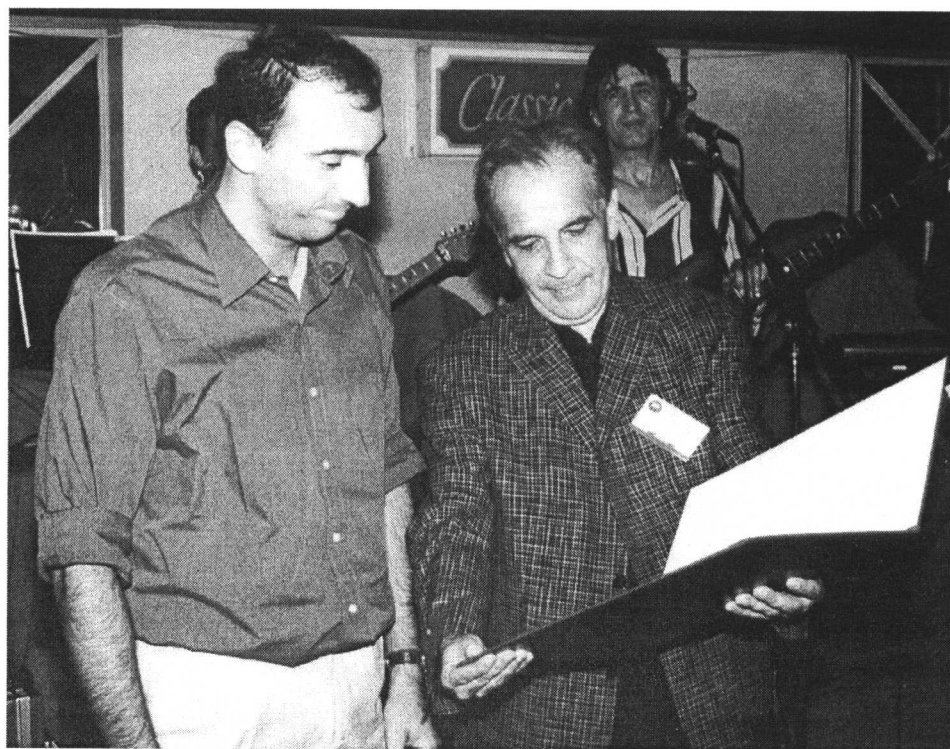
P. Igić accepts the award from N. Stojadinović

**MIEL 2000 Best Paper Award
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Microelectronics Reliability**

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for

Rise-Time Effects in ggnMOST under TPL Stress



G. Boselli accepts the award from N. Stojadinović

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